

The investigation of new materials, devices and techniques to improve the performance of telecommunications, spectroscopy and radar systems applications, has caused that the study of non-stationary effects of space charge in semiconductor structures be a strategy research area in the field of high speed semiconductor devices. Therefore, this book focuses in the study of the non-stationary effects of the space charge in semiconductor structures, where the nonlinear wave interaction in active media may serve to improve the high-frequency performance of semiconductor devices.

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